

## SAM<sup>TM</sup> data sheet SAM-810-5-1ps-x, $\lambda$ = 810 nm

Laser wavelength  $\lambda = 810 \text{ nm}$ 

High reflection band (R > 90%)  $\lambda$  = 785 .. 830 nm

Absorbance  $A_0 = 5 \%$  Modulation depth  $\Delta R = 3 \%$  Non-saturable loss  $A_{ns} = 2 \%$ 

Saturation fluence  $\Phi_{sat} = 110 \,\mu\text{J/cm}^2$ 

Relaxation time constant  $\tau \sim 1 \text{ ps}$ 

Damage threshold  $\Phi_{\text{sat}} = 2 \text{ mJ/cm}^2$ 

Chip area 4mm x 4mm; other dimensions on request

Chip thickness 450 µm

Protection the SAM is protected with a dielectric front layer

Mounting option **x** denotes the type of mounting as follows:

x = 0
x = 12.7 g
x = 25.4 g
x = 12.7 s
x = 25.4 s
x = 25.4 s
x = 25.0 w
x

## Low intensity spectral reflectance

